

1 **Colloidal Tin Sulfide Nanosheets:**
2 **Formation Mechanism, Ligand-mediated Shape Tuning and Photo-detection**

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12
13 **Abstract**

14 Colloidal materials of tin(II) sulfide (SnS), as a layered semiconductor with a narrow band
15 gap, are emerging as a potential alternative to the more toxic metal chalcogenides (PbS, PbSe,
16 CdS, CdSe) for various applications such as electronic and optoelectronic devices. We
17 describe a new and simple pathway to produce colloidal SnS nanosheets with large lateral
18 sizes and controllable thickness, as well as single-crystallinity. The synthesis of the
19 nanosheets is achieved by employing tin(II) acetate as tin precursor instead of harmful
20 precursors such as bis[bis(trimethylsilyl)amino] tin(II) and halogen-involved precursors like
21 tin chloride, which limits the large-scale production. We successfully tuned the morphology
22 between squared nanosheets with lateral dimensions from 150 to about 500 nm and a
23 thickness from 24 to 29 nm, and hexagonal nanosheets with lateral sizes from 230 to 1680 nm
24 and heights ranging from 16 to 50 nm by varying the ligands oleic acid and trioctylphosphine.
25 The formation mechanism of both shapes has been investigated in depth, which is also
26 supported by DFT simulations. The optoelectronic measurements show their relatively high
27 conductivity with a pronounced sensitivity to light, which is promising in terms of photo-
28 switching, photo-sensing, and photovoltaic applications also due to their reduced toxicity.

29

30 **Introduction**

31 Two-dimensional (2D) metal chalcogenides serve as building blocks in various applications,
32 including catalysis, batteries, solar cells, optoelectronics, and thermoelectric energy
33 harvesting, owing to their unique size- and shape-dependent optical and electrical properties
34 compared to 0D nanoparticles and also 1D nanorods.¹⁻⁸ 2D nanomaterials comprising lead or
35 cadmium chalcogenides such as PbS, PbSe, CdS and CdSe have been intensively investigated.
36 They exhibit tunable optoelectronic properties, which often are superior to their bulk
37 counterparts.⁹⁻¹² However, they also display high toxicity, which hampers their applicability.
38 To mitigate this problem, further studies of more environmentally friendly and less toxic
39 semiconductors are necessary. One promising class of materials are tin chalcogenides.¹³⁻¹⁵ In
40 particular, tin(II) sulfide (SnS), a p-type semiconductor with an indirect bulk band gap of 1.07
41 eV and a direct band gap of 1.3 eV, shows both a high absorption coefficient and a good hole
42 mobility.^{16, 17} Typically, SnS adopts a layered orthorhombic (OR) crystal structure (*space*
43 *group: Pbnm*). SnS can be described as highly distorted rock salt structure with atomic double
44 layers, which are covalently bonded in the plane and van-der-Waals bonded in the vertical *b*
45 direction ($a = 4.33 \text{ \AA}$, $b = 11.19 \text{ \AA}$, $c = 3.98 \text{ \AA}$). Latter is due to a chemically inert surface
46 without any dangling bonds, which leads to its relatively high chemical stability and promotes
47 2D morphology.^{18, 19} Recently, theoretical and experimental studies showed extraordinary
48 properties of 2D SnS such as selected valleys optical excitation, ferroelectric and piezoelectric
49 properties, which further motivate the development of cheap and safe methods for 2D
50 morphology.^{20, 21}

51 Recently, several studies focused on the synthesis of 2D SnS nanostructures. However, most
52 of the materials are produced by demanding physical methods such as physical vapor
53 deposition, molecular beam epitaxy and mechanical exfoliation, which usually yield
54 polydisperse, irregular-shaped SnS nanosheets (NSs).²²⁻²⁴ Compared to physical methods,
55 colloidal syntheses can produce NSs from solution, assisted by surfactants to control the
56 growth with uniform lateral dimensions, regular faceted edges and tunability. Such
57 nanostructures can be processed by simple means, as there are spin coating and drop casting,²⁵
58 which is a prerequisite for efficient and inexpensive manufacture of super-assembled
59 structures or deposition on flexible substrate for further applications.²⁶ However, most of the
60 published synthetic recipes for SnS (analogically SnSe) yield mainly nanocubes and
61 nanoparticles.^{16, 27, 28} A few syntheses of colloidal 2D SnS nanosheets have been reported so

62 far, but most of them are synthesized with halogen involved tin precursors (e.g. tin(IV)
63 tetrachloride pentahydrate, tin(II) chloride) or with the assistance of hexamethyldisilazane
64 (HMDS) for 2D nanomaterial formation.^{16, 29-31}

65 The colloidal synthesis of 2D SnS NSs in the here presented work uses tin(II) acetate as tin
66 precursor, which can be partly converted into the corresponding Sn-oleate complex during the
67 conditioning step in the presence of oleic acid and partly serving as ligand for NS formation.
68 In this process, no halogen ions are involved (e.g. through tin(II) chloride or tin(IV) chloride).
69 Halogen ions in the SnS NS synthesis have been reported to be fully complexed by HMDS
70 and be completely removed to avoid the inhibition of the formation of SnS NSs.^{31, 32} Thus, the
71 introducing of chloride ions is not necessary. The precursor bis[bis(trimethylsilyl)amino]
72 tin(II) has been reported to yield rectangular NSs with a size of $7 \mu\text{m} \times 20 \text{ nm}$.³³ However,
73 this type of tin precursor is very flammable with low stability and high reactivity. Here, we
74 introduce a halogen-and-HMDS-free synthesis of NSs, involving no flammable precursor as
75 well. It shows that oleic acid (OA) and trioctylphosphine (TOP) amounts have strong control
76 over shape and size (150-1680 nm). Based on experimental data and DFT calculations, we
77 rationalize the shape changes of SnS NSs and propose an approach where the shape can be
78 tuned between squared and hexagonal. The samples' crystal phase can be obtained as single-
79 crystalline OR without other phases involved (e.g. pseudotetragonal phase from byproducts).
80 We investigated in depth the mechanism of ligand-facet interaction to form NSs with different
81 size and shape, as well as the function of the precursors. Eventually, by contacting individual
82 NSs, their performance in terms of conductivity and photoconductivity has been investigated,
83 revealing their outstanding optoelectronic properties.

84

85 **Experimental Section**

86 **Materials.** Tin(II) acetate (TA, 100%), oleic acid (OA, technical grade, 90%),
87 trioctylphosphine (TOP, 97%), diphenyl ether (DPE, Reagent plus, $\geq 99\%$), toluene,
88 dimethylformamide (DMF) were purchased from Sigma-Aldrich and were all used as-
89 received without additional purification. Thioacetamide (TAA, ACS Reagent Grade, 99%)
90 was bought from Fisher Scientific (Acros Organics). Thioacetamide, trioctylphosphine and
91 tin(II) acetate were all stored in a glovebox.

92 **Synthesis of square-like 2D SnS nanosheets.** In a typical synthesis, a round-bottom three-
93 neck 50 mL flask was used terminated by a condenser, a septum and a thermocouple. 59.2 mg
94 (0.25 mmol) of TA, 0.2 mL (0.64 mmol) of OA and 0.5 mL of TOP (1.0 mmol) were
95 dissolved in 10 mL of DPE. The mixture was degassed and dried under vacuum for 2 h at
96 75°C, partially transforming tin acetate into tin oleate and removing the free acetic acid from
97 the system as well. After the vacuum step, the mixture was heated to 230 °C under nitrogen
98 flow. After temperature stabilization (15 min), 19.5 mg (0.26 mmol) of TAA in 0.2 mL of
99 DMF was injected rapidly into the reaction solution. After 5 min, the heating mantle was
100 removed and the resultant solution was left for cooling to room temperature. The resultant
101 nanostructures were then purified by centrifugation with toluene at 4000 rpm for 3 min (2-3
102 times). The product could then be re-suspended in toluene for further characterization or
103 storage. To investigate the influence of different parameters, the other reaction parameters are
104 kept constant.

105 **Characterization.** Transmission electron microscope (TEM) images and selected area
106 electron diffraction (SAED) were obtained using a JEOL-1011 operated at 200 kV. All the
107 TEM samples were prepared by dropping a 10 μL diluted toluene dispersion onto carbon-
108 coated TEM grids followed by solvent evaporation at ambient conditions. The high resolution
109 (HR) TEM images were performed on a Philips CM 300 UT microscope operated at 200 kV.
110 The X-ray diffraction (XRD) patterns were obtained employing a Philips X'Pert System with
111 Bragg-Brentano geometry, together with a copper anode at an X-ray wavelength of 0.154 nm.
112 The samples were prepared by drop casting of a well suspended NS solution on silicon
113 substrates. The surface topology data were obtained on an atomic force microscope (AFM)
114 from JPK Instruments in intermittent contact mode. The samples were prepared by drop-
115 casting a diluted NS suspension on a silicon chip. The samples were also measured by

116 scanning electron microscopy (SEM) with a LEO GEMINI 1550 microscope for morphology
117 information.

118 **Device preparation.** SnS NSs suspended in toluene were spin-coated on silicon wafers with
119 300 nm thermal silicon oxide as the gate dielectric. The highly doped silicon was used as back
120 gate. The individual NSs were contacted by e-beam lithography followed by thermal
121 evaporation of Ti/Au (1/55 nm) and lift-off.

122 **Device measurements.** Immediately after device fabrication, the samples were transferred to
123 a probe station (Lakeshore-Desert) connected to a semiconductor parameter analyzer (Agilent
124 B1500a). All the measurements have been performed in vacuum at room temperature. The
125 vacuum chamber has a view port above the sample which is used for sample illumination. For
126 illumination of the NSs, a red laser (627 nm, 1-16 mW) with a spot size of 2 mm was used.

127 **DFT simulations.** In order to evaluate the adsorption energies of the ligands on different
128 crystal facets simulations based on density functional theory (DFT) were employed. For that
129 the crystal geometry had been kept fixed to the experimental values for OR-SnS and the
130 ligands were free to relax by geometry optimization. We used the versatile software package
131 CP2K with the PADE LDA functional, the DZVP basis set, and a corresponding GTH-PADE
132 potential. An individual SnS nanocrystal with 224 Sn and 224 S atoms and the respective
133 ligand molecules are simulated with periodic boundary conditions where the box dimensions
134 are sufficiently large to avoid interaction between virtual neighboring molecular structures.

135 **Results and Discussion**

136 In the following we discuss the influence of various parameters on the synthesis of SnS
137 nanosheets. It allows drawing conclusions on the formation mechanism and the
138 crystallography. Eventually, we demonstrate their optoelectronic response.

139 **Synthesis of colloidal square-like SnS nanosheets.** TA, OA and TOP in DPE were degassed
140 at 75°C and then heated to a reaction temperature of 230°C under nitrogen flow, followed by
141 the hot injection of TAA, as sulfide precursor, to obtain fast nucleation and growth of 2D
142 NSs. To guarantee the repeatability of the procedure, we kept the injection volume constant
143 (0.2 mL) for all experiments. During the preheating and degassing phase, TA as tin precursor
144 was partly transformed to tin oleate in the presence of OA. When tin (II) chloride was used as
145 precursor, only irregularly shaped NSs and byproducts were formed with an otherwise
146 unchanged recipe (Figure S1). A TEM image of square-like SnS NSs with a lateral size of
147 approximately 460 nm is shown in Figure 1a. SAED (Figure 1b) reveals single-crystallinity
148 due to the well-ordered dot pattern, which matches the list of reflections of OR-SnS bulk (The
149 International Centre for Diffraction Data (ICDD) card 00-039-0354), respectively showing the
150 diffraction planes (200), (101), and (002). The X-ray diffractogram (Figure 1c) of the
151 capillary powder sample is also consistent with the crystallography for OR-SnS bulk. For the
152 drop-casted SnS NSs film, the two pronounced peaks (040) and (080) are observed,
153 representing the highly textured [010] orientation, which indicates that it is the one
154 corresponding to the thickness. The Scherrer analysis of the (040) peak in the film sample
155 yields a thickness of 29 nm for the sample shown in Figure 1c. A SEM image (Figure 1d)
156 gives an overview on the morphology of the NSs, which shows the squared NSs with smooth
157 surface and some squared NSs with truncated edges. An AFM image of the square-like SnS
158 NSs is shown in Figure S2 and the measured thickness is 31 nm.

159 **Influence of trioctylphosphine on the synthesis of square-like single-crystal SnS**
160 **nanosheets.** The synthesis of SnS NSs proceeds in two steps. First, the complexation of the
161 tin precursor in the presence of OA happens before the injection of the second precursor.
162 Second, the reaction between the tin and the sulfur precursor takes place to form nuclei, which
163 is followed by the growth process to produce SnS NSs. Theoretically, the crystal facets with
164 lower surface energy have a slower growth speed in order to minimize the total surface energy
165 of the whole crystal based on the Gibbs-Curie-Wulff theorem and the Wulff construction.^{34, 35}
166 Furthermore, the reason for anisotropic growth of 2D nanocrystals is mainly due to the

167 different surface energies of the facets according to the selective-adsorption of ligands. Thus,
168 different growth speeds on each facet capped with certain ligands lead to the final shape of
169 nanostructures. When there is no TOP and no OA in the synthesis, SnS nanoparticles and
170 squared nanoplatelets (≤ 100 nm) are obtained (Figure S3). This indicates that the acetate can
171 facilitate the formation of 2D nanostructures without TOP or OA in the synthesis, which is
172 also supported by DFT simulations on the adsorption energy in Table 1. They show that
173 acetate (AA^-) as ligand binds stronger to the (100) and (101) side facets, also binds strong to
174 (010) facets, which could lead to truncated rectangular small nanoplatelets. However, it is
175 shown that only acetate can mostly produce nanoparticles. When no TOP was involved in the
176 synthesis, spherical nanoparticles and hexagonal NSs (Figure 2a, S3b) were synthesized with
177 a constant amount of OA (0.64 mmol) and all other parameters unchanged. This is due to the
178 strong bond of oleate on (100) and (101) (or {101}), which facilitate the hexagonal shape
179 (elongated facet is (100), Figure S3b). A TEM image of the synthesis with 0.1 mmol TOP
180 (Figure 2b) shows that most of the products were nanoparticles, accompanied by small
181 hexagonal-shaped and square-shaped nanoplatelets. The appearance of square-shaped
182 nanocrystals is consistent with the simulation data for TOP, revealing that adsorption energy
183 on {101} facets are larger than others. Compared to the product with only OA ligands in
184 Figure 2a, this indicates that this small amount of TOP still exerts its influence to maintain the
185 2D square-shaped nanostructure formation (~ 160 nm). More squared sheets with increased
186 edge lengths of 240 nm were produced together with less irregular nanoparticles when 0.5
187 mmol of TOP was used (Figure 2c). 1.0 mmol TOP led to larger (nearly 460 nm) squared
188 sheets without byproducts. Further, doubling the amount of TOP made no significant
189 difference. Therefore, TOP plays an important role in retaining the growth of square-shaped
190 NS with the acetate ligands, while OA facilitates the formation of hexagonal shaped
191 nanostructures.

192 The XRD data (Figure 2f) display a more and more prominent (040) peak compared to other
193 suppressed peaks with increasing TOP amount, which can indicate that more squared and
194 larger 2D nanostructures as well as less byproducts (such as nanoparticles or nanoplatelets)
195 were produced. The intensity of the diffraction peak at 44.04° is reduced when the amount of
196 TOP increases from 0.0 mmol to 2.0 mmol TOP. This diffraction peak does not match the
197 standard diffraction pattern of OR-SnS bulk but this peak is close to (220) of zinc blend (ZB)
198 phase (43.8°). Theoretically, ZB SnS is a metastable phase, which is only kinetically stable
199 and protected by a certain specific energy barrier avoiding the transformation to OR-SnS.^{36,37}

200 However, it can be better explained by the convolution of 43.9° and 44.1° of pseudotetragonal
201 structure (PT), as more stable crystal phase under given condition.¹⁶ The XRD measurement
202 for the powder sample in capillary (Figure S4) demonstrates more clearly that the samples
203 using 0.1 mmol of TOP show a mixture of OR and PT crystal structures, together with several
204 small peaks ($2\theta = 32.7^\circ, 35.5^\circ$) stemming from the planes $(12\bar{1})$, (031) of crystalline sulfur
205 (ICDD card 01-072-2402). In addition, the peaks at $30.7^\circ, 26.5^\circ$ also stand for (101) and (021)
206 of PT. The SAED also shows the nanosheet is OR-type and PT phase belongs to the
207 byproduct (nanoparticle, Figure S5a, b). An increasing yield of crystalline SnS NSs could be
208 obtained when we used TOP in amounts of up to 1.0 mmol in our case, with the gradually
209 disappearance of PT particle product.

210 The thickness values calculated from XRD are in the range from 24 to 29 nm with a raising
211 TOP amount (Figure S6). The SAED patterns of a single truncated square sheet from the
212 synthesized sample with 1.0 mmol TOP (Figure 3) with two non-truncated diagonal corners
213 and other two truncated corners are investigated. The HRTEM images (Figure 3b, c) and
214 corresponding FFTs (inset) reveal the four planes corresponding to four sides of the square-
215 shaped sheet, are $\{101\}$ planes. This is also confirmed by the electron diffraction patterns in
216 Figure 3d. The SAED pattern demonstrates the facets of (200) , (002) and (101) which also are
217 identified in the corresponding TEM images in Figure 3a (SAED patterns are rotated in
218 respect to TEM image by the instrumentation). The truncated facets are found to be (100) and
219 $(\bar{1}00)$ facets. Figure 3e shows a model for SnS NSs with square shape (Figure 3e (1)),
220 truncated square shape (Figure 3e (2)) and highly truncated or hexagonal shape (Figure 3e
221 (3)). The atomic arrangements of the (101) and $(\bar{1}01)$ facets (Figure 4a, b) show that Sn and S
222 atoms are alternating ordered. In principle, each S (or Sn) atom in these facets has three
223 bonds, from which one bond is always forming a bond with S (or Sn) perpendicular to the
224 facets. As L-type ligands, TOP prefers to bind to metal centers. Our DFT simulations (Table
225 1) show the interaction between TOP and Sn atoms on the (101) facet and also demonstrate
226 that TOP binds to the $\{101\}$ facets most strongly and it displays a weak preference on the
227 (010) facet. Therefore, acetate ligands lead to squared 2D SnS nanoplatelets and TOP can help
228 to maintain the square shape and enlarge the size of the nanoplatelets to large nanosheets.

229 **Influence of the oleic acid amount in the synthesis of square-like single-crystal SnS**
230 **nanosheets.** When only TOP and no OA is introduced in the synthesis, small squared sheets
231 and nanoparticles both appear in the product (Figure 5a, Figure S8a). This matches the

232 simulation data for TOP, indicating that TOP can enhance the formation of (101)-facet square
233 NSs (Figure S8a). Further, we investigated the influence of the OA amount on the
234 morphology of synthesized SnS NSs, keeping TOP (1.0 mmol) and other parameters constant.
235 The TEM images of the synthesis using 0.32 mmol to 0.64 mmol of OA in Figure 5a-c show a
236 lateral size change from 180 nm to 380 nm and thickness increase from 16 nm to 29 nm
237 (derived from XRD, no shape change, still square-like sheets), together with a higher degree
238 of uniformity in lateral-size. Moreover, squared NSs, as well as nanoparticles were observed
239 with a low amount of OA ($OA \leq 0.64$ mmol, TA: OA ratio $\leq 1: 2.5$). This is due to that the
240 strong adsorption energy of TOP on (101) dominates (Table 1), which assist the formation of
241 squared sheets with the original acetate in the synthesis. The simulations are performed using
242 simplified molecules for OA and oleate (represented by butyric acid BA and butyrate BA⁻).
243 The hexagonal shape starts to appear when the OA amount is larger than 2 mmol, which we
244 consider as the minimum amount of OA for the formation of hexagonally shaped sheet.
245 Lateral size and thickness values both increase largely (33 nm to 53 nm) when 12 times more
246 OA than TA is applied ($OA \geq 3.2$ mmol, TA: OA ratio $\geq 1: 12$). Based on the law of mass
247 action, the higher the amount of OA, the higher the possibility for OA to bind to the surface of
248 the crystals, substituting the oleate. OA (L-type ligand) is a weaker ligand than oleate (X-type
249 ligand), which facilitates the monomers to react on the crystal surface compared to the case of
250 oleate as ligands, helping to grow larger and thicker sheets under otherwise unchanged
251 conditions. Higher OA amounts (≥ 3.2 mmol) trigger the shape change from square-like to
252 hexagonal nanostructures and strongly influence the size (TA: OA ratio $\geq 1: 12$, especially
253 1:25). Analysis of the lateral sizes calculated from TEM images (Figure 5) shows a dramatic
254 increase (from 160 nm to 1600 nm, OA used from 0.32 mmol to 6.34 mmol). This confirms
255 that OA plays a major role in the size and shape tuning from squared to hexagonal SnS NSs.
256 This is due to the largest adsorption energy of neutral OA ligands (represented by butyric acid
257 BA, Table 1) on (100) facets compared to those on (101) or (010) facets, facilitating the
258 formation of hexagonal NSs with elongated edges when there is an excess of OA ligands (\geq
259 3.2 mmol) (Figure S8b, with 6.4 mmol OA). XRD measurements show a further pronounced
260 (040) peak and a more suppressed (220) peak for higher OA amount, indicating that a suitable
261 quantity of OA could lead to stable OR-SnS nanostructures. Size and shape evolution of SnS
262 NSs is sketched in Figure 6 and shows how OA with TOP influences the formation of SnS
263 NSs.

264 **Effect of the precursor amount.** The amounts of precursors will define the numbers of
265 nuclei for further growth. We found that with an increasing amount of tin precursor, there is a
266 dramatic drop in size (Figure 7). When 0.025 mmol of TA is used, the lateral size reaches 826
267 nm, along with 36 nm of thickness (Figure 7). In the case of lower TA amount (<0.25 mmol),
268 larger and thicker sheets are formed after the injection of sulfide source. The less the amount
269 of tin source, the lower the number of nuclei that form, which then causes the formation of
270 larger and thicker NSs. When the amount reaches 0.5 mmol TA, nanoparticles appear due to
271 an excess of acetate ligands. Different amounts of sulfur source are also investigated to
272 elucidate the influence on the SnS NS synthesis (Figure S9). Concerning the amount of sulfur
273 precursor, the TEM images reveal that lower amounts (≤ 0.13 mmol) only lead to irregular
274 shaped NSs. But these irregular sheets are still highly crystalline with OR crystal structure
275 (Figure S10). This is attributed to the lack of sulfur monomers for further growth of NSs.
276 XRD measurements also demonstrate that with an increasing amount of sulfur precursor, the
277 (040) and (080) peaks are more pronounced and other peaks are more suppressed (Figure S9).
278 When the amount of TAA reaches 0.26 mmol, lateral size and thickness begin to level off.

279 Therefore, we propose a growth mechanism for the formation of 2D SnS nanosheets based on
280 our approach. Firstly, the tin ions are coordinated by acetate (Sn-acetate), as tridentate
281 bridging ligands with certain chelate character, forming strongly distorted trigonal bipyramid
282 for the first coordination sphere.³⁸ TAA thermally decomposes by hot injection, producing S^{2-}
283 for further reaction with Sn^{2+} ions. Therefore, SnS nuclei are formed after TAA
284 decomposition, passivated by the ligands on the surface of nuclei. With the injection of the
285 sulfur source, the acetate ligands trigger the formation of SnS nanoparticles and squared
286 nanoplatelets (≤ 100 nm) without OA and TOP in the reaction due to the dominated
287 passivation on {101}, (100) and (010) facets by acetate. We introduce OA in the synthesis
288 (0.64 mmol), hexagonal sheets and small nanoparticle byproducts are obtained, whereas
289 square sheets are prepared with TOP involved (1.0 mmol) in the synthesis without OA,
290 because of strong bond of oleate ligands on (100) and {101}. When OA is applied and the
291 amount of OA is lower than 3.2 mmol together with 1.0 mmol TOP, Sn-acetate is partly
292 replaced with Sn-oleate during the vacuum step, leading to the formation of still squared SnS
293 NSs (~460 nm) without byproducts. However, hexagonal NSs are formed when the OA
294 amount is higher with a constant TOP amount. Thus, the shape of the NSs is due to the
295 balance between TOP and OA, as well as the original acetate ligands. For that, tuning the
296 amount of TOP and OA can tune the shape between squared and hexagonal NSs. When the

297 right ratio of TOP/OA is used in the synthesis, the product can be obtained as pure OR-SnS
298 nanosheets without PT-type byproducts.

299 **Electrical measurements.** In order to investigate the potential application of the nanosheets,
300 we measured the conductivity and photoconductivity of individually contacted SnS NSs.
301 Figure 8a shows the I-V characteristics of the NSs in dark and under different illumination
302 powers. The dark conductivity of the NSs is relatively higher than comparable materials such
303 as colloidal PbS nanosheets (7.9 S/m, which is up to one order of magnitude higher than the
304 conductivity of PbS nanosheets).³⁹ By illuminating the sheets with a red laser ($\lambda = 627$ nm),
305 the current increases, which is attributed to an increased carrier concentration due to the optical
306 excitation and generation of electron-hole pairs. The sensitivity of the device, defined by $(I_{ill}$
307 $- I_{dark})/I_{dark}$ reaches 0.95. Further, we calculated the spectral response R_λ and detectivity D^*
308 by employing the following equations.

$$309 \quad R_\lambda = \frac{I_{ph}}{P_{light}A}$$
$$310 \quad D^* = \frac{R_\lambda A^{0.5}}{(2eI_{dark})^{0.5}}$$

311 In these equations, I_{ph} is the photogenerated current, P_{light} is the laser power density (50
312 mWcm^{-1}), A is the effective area of the device ($0.5 \mu\text{m}^2$), and e is the elementary charge.⁴⁶
313 The photodetectors based on our NSs show to have a spectral response of $\sim 3 \times 10^3 \text{ AW}^{-1}$ and a
314 detectivity of $\sim 4 \times 10^9$ Jones. The performance of these NSs is superior compared to the
315 previously reported works on this material under similar conditions.⁴⁰ This is another proof
316 for the high quality of the crystals and its low defect density.

317 By increasing the beam power, higher photocurrents are detected which is due to higher
318 amounts of electron-hole pairs. However, as can be seen in Figure 8b, the dependence of the
319 photoconductivity to the beam power experiences saturation in higher intensities. With an
320 intermittent illumination, we also demonstrate the stability of the photocurrent. Similar values
321 are achieved for the photoconductivity under illumination with 25 mW. Fast transitions
322 between the on state and the off or dark state are observed (Figure 8c), which is an important
323 requirement for photo-detectors. This is a further indicator for the high quality of the crystals
324 and the lack of defects.⁴¹ Also, through such measurements, clear change of the photocurrent
325 can be observed by changing the beam power, while stability and speed of the system remain

326 unchanged (Figure 8d). These measurements illustrate the potential of the produced SnS NSs
327 for cost effective non-toxic optoelectronics (e.g. photo-detectors).

328 **Conclusion**

329 A facile and simple colloidal method has been explored to synthesize large (150 nm-1680 nm,
330 thickness from 16 nm to 50 nm) single-crystalline SnS NSs in the presence of oleic acid and
331 trioctylphosphine as co-ligands together with two precursors, tin acetate and thioacetamide.
332 Therefore, no metal halides (e.g. tin chloride) or flammable organo-metallic precursors are
333 introduced. The two ligands (OA (also oleate), TOP) are discovered to play a critical role in
334 tuning the shape and size of the SnS NSs in addition to the original ligand, the acetate. The
335 development of the final product involves the steps of instantaneous nucleation and
336 anisotropic growth by the optimized balance of involved ligands. The NSs undergo a shape
337 change between hexagonal sheets and square-like sheets by tuning the ligand quantity (acetate,
338 oleate, OA, TOP). The crystal phase can be optimized from PT (coming from nanoparticle
339 byproducts) and OR crystal structure (coming from nanosheets) into single-crystalline
340 nanosheets of OR structure only. The conductivity and photoconductivity measurements
341 demonstrate their high potential for optoelectronic applications such as photo-sensors and
342 photo-switches.

343

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350

351 **Supporting information**

352 Further experimental data are presented. In particular, detailed TEM images on the shape and
353 crystallographic structure of the nanosheets, AFM images to determine the height of the

354 materials, XRD measurements to determine the crystallographic phase. Beyond, SEM results
355 are shown.

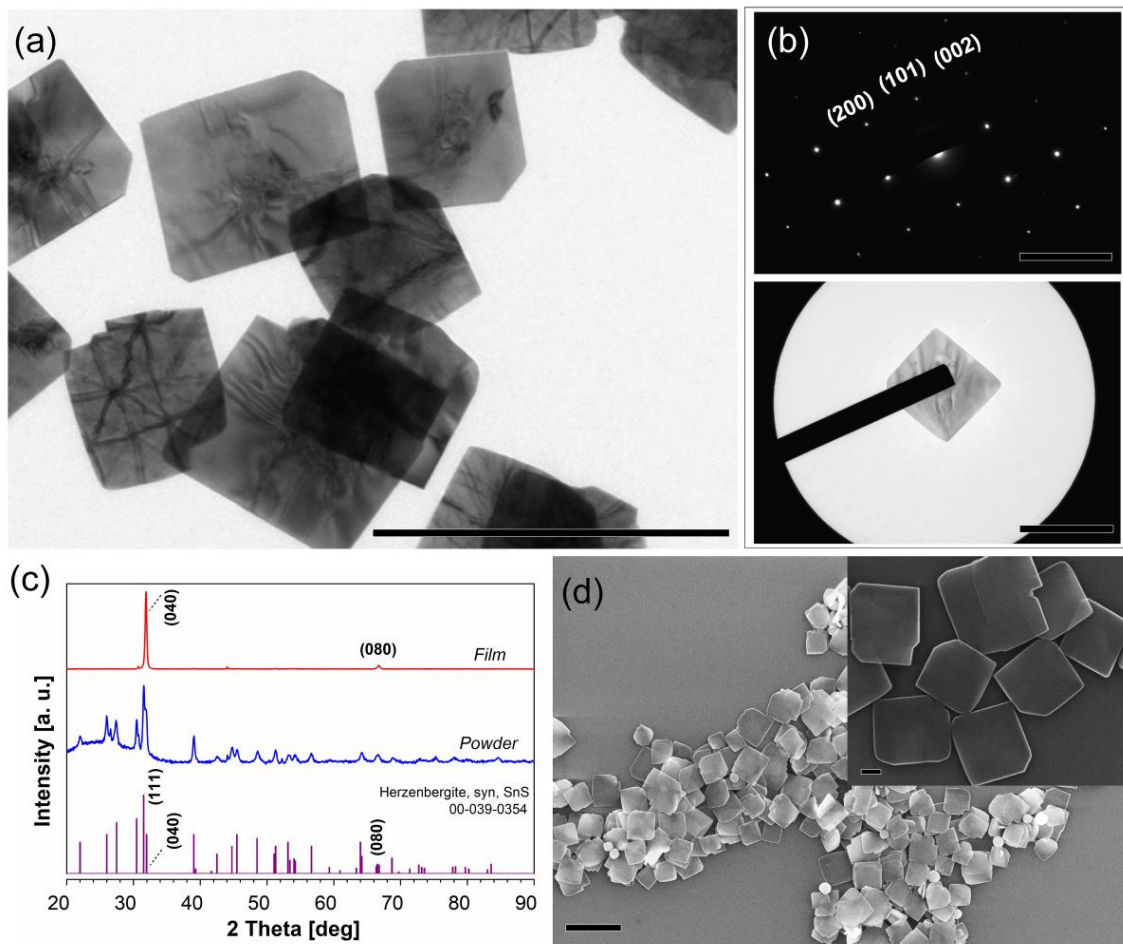
356

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360



362

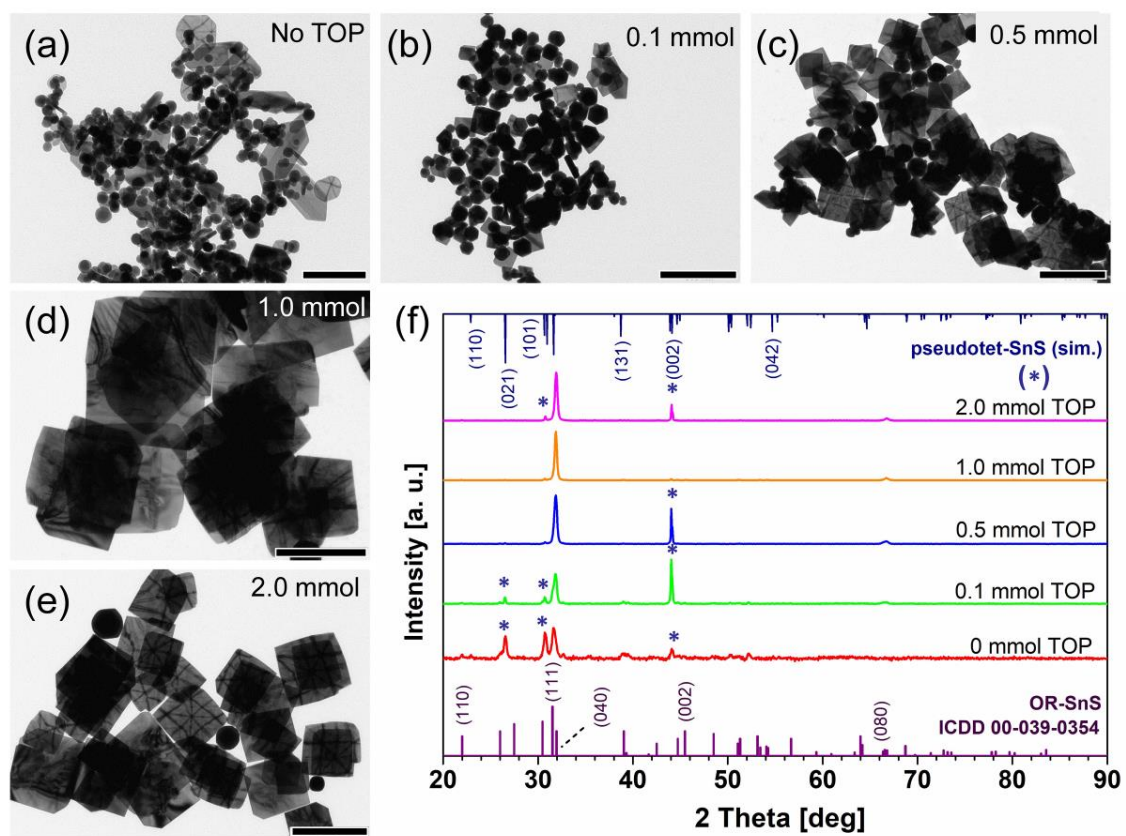
363 **Figure 1.** (a) TEM images of square-like SnS NSs synthesized with the standard synthesis.
364 Scale bar = 1 μm. (b) SAED pattern of a single nanosheet and corresponding TEM image. (c)
365 XRD patterns for SnS NSs drop-casted on a Si wafer (thin film) and a powder sample in a
366 capillary tube. (d) SEM images of SnS NSs (scale bar = 1 μm, inset: larger magnification:
367 scale bar = 100 nm).

368

369 **Table 1.** Adsorption energy [eV] of ligand molecules on the (100), (101), (010) facets of SnS
 370 calculated by the density functional theory (DFT) method. The simulations were performed
 371 using the full version of acetate (AA⁻) and simplified molecules for TOP, OA and oleate
 372 (triethylphosphine (TEP) and tributylphosphine (TBP) for TOP, butyric acid (BA) for OA,
 373 and BA⁻ (butyrate) for the oleate). The simplified TOP, OA and oleate molecules were used to
 374 enable reasonable calculation times and to avoid additional contributions by the adsorption of
 375 the side chains. Anyhow, simulations on different chain lengths (C2 and C4) show that the
 376 tendencies are similar.

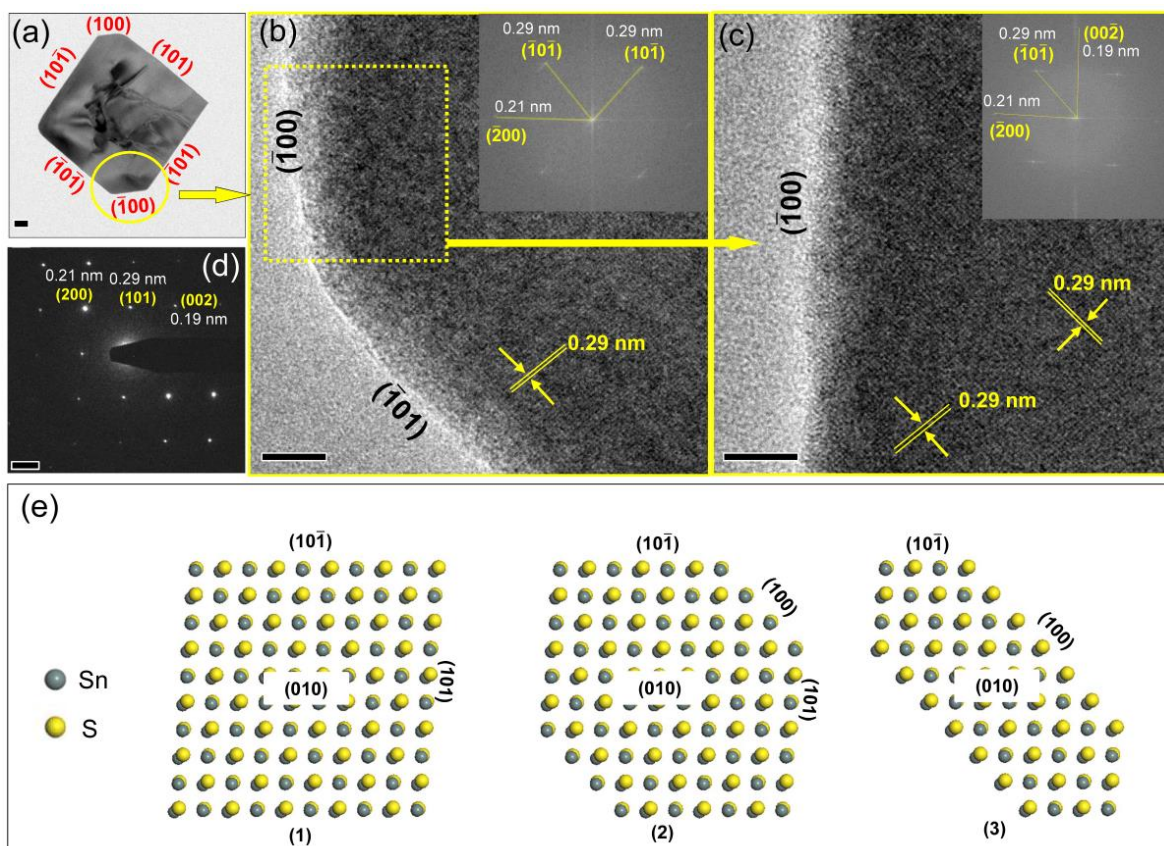
	SnS-101 side facet (isotropic)	SnS-100 side facet (anisotropic-zigzag)	SnS-010 top facet (Top or down)
TEP (C2)	1.834	1.842	0.651
TBP (C4)	2.061	2.060	0.772
AA ⁻ (C2)	3.661	4.453	2.506
AA (C2)	0.988	1.358	0.551
BA ⁻ (C4)	3.635	4.355	2.547
BA (C4)	1.076	1.120	0.623

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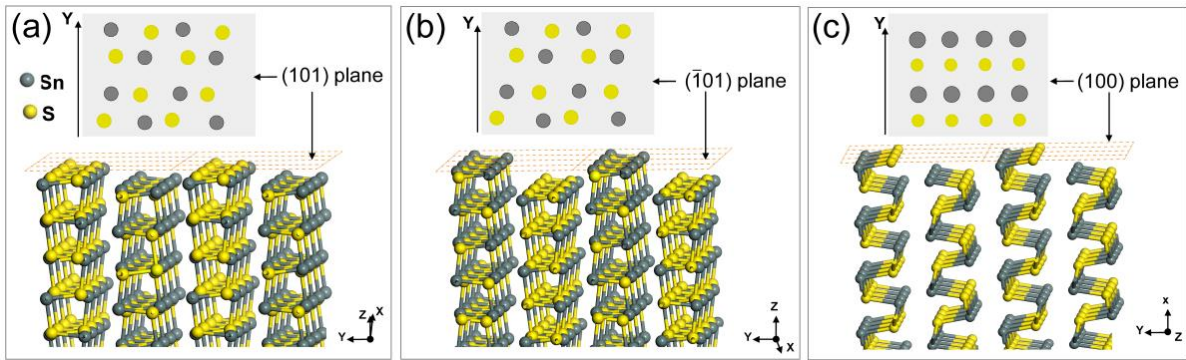
380 **Figure 2.** (a-e) TEM images of 2D SnS nanostructures with different TOP amounts (0 - 2.0
 381 mmol). Scale bar is 200 nm for a, and 500 nm for b-e. (f) Powder XRD patterns of SnS NSs.



382

383 **Figure 3.** (a) TEM image of a single SnS NS from the standard synthesis with two non-
 384 truncated diagonal corners and other two truncated corners. The HRTEM image reveals the
 385 lattice spacing of 0.29 nm (b, c), which is consistent with the spacing of {101} planes. The
 386 SAED patterns (d) shows the lattice fringes of crystal facets (200), (002) and (101). The
 387 corresponding facets of $(\bar{1}00)$, $(\bar{1}01)$ are recognized based on the FFT analysis in inset of b
 388 and c, confirming the faceting in a. A set of atomic models of SnS NSs with the shape
 389 changing from squared to hexagonal (e). All these three models drawn here contained two
 390 layered atoms and that was why certain overlapping could be seen from the figure (grey Sn
 391 atoms overlap yellow S atoms, or yellow S atoms overlap grey Sn atoms). The scale bar = 50
 392 nm in a, 5 nm in b and c, 5 μm in d.

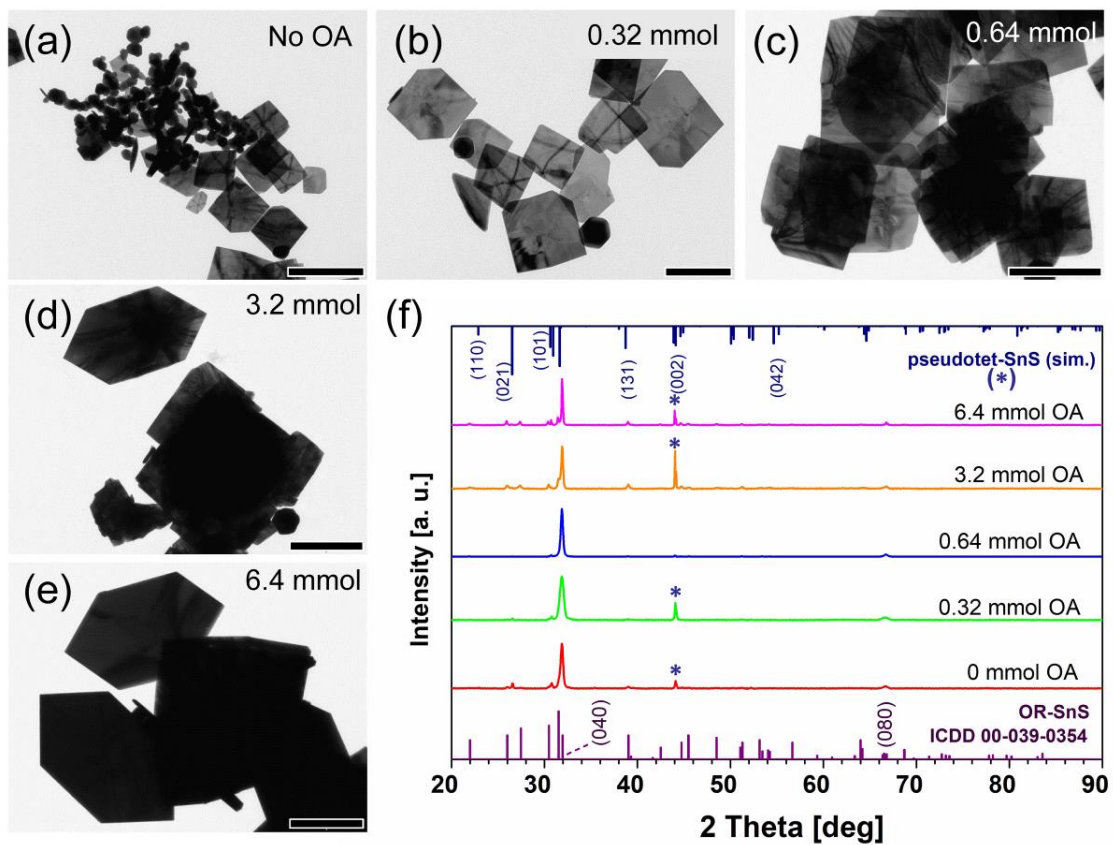
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395 **Figure 4.** (a-c) The atomic arrangements in (101), $(\bar{1}01)$ and (100) planes of SnS nanocrystals
 396 respectively. The top views of each model are also shown to demonstrate the exposed atoms
 397 on these three facets.

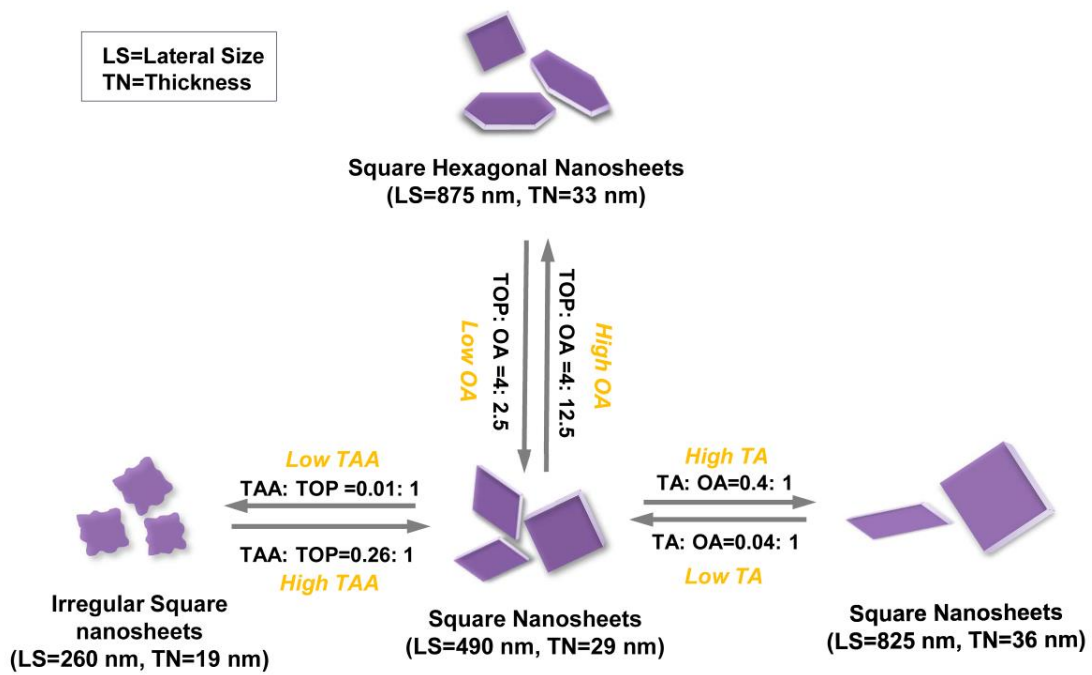
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400 **Figure 5.** (a-e) Shape and size change of SnS nanoparticles to nanosheets synthesized using
 401 varied OA amounts (0 - 6.34 mmol). Scale bars correspond to 500 nm, 200 nm, 500 nm, 1
 402 μm, and 1 μm respectively from a-e. (f) Powder XRD patterns of SnS NSs from a-e.

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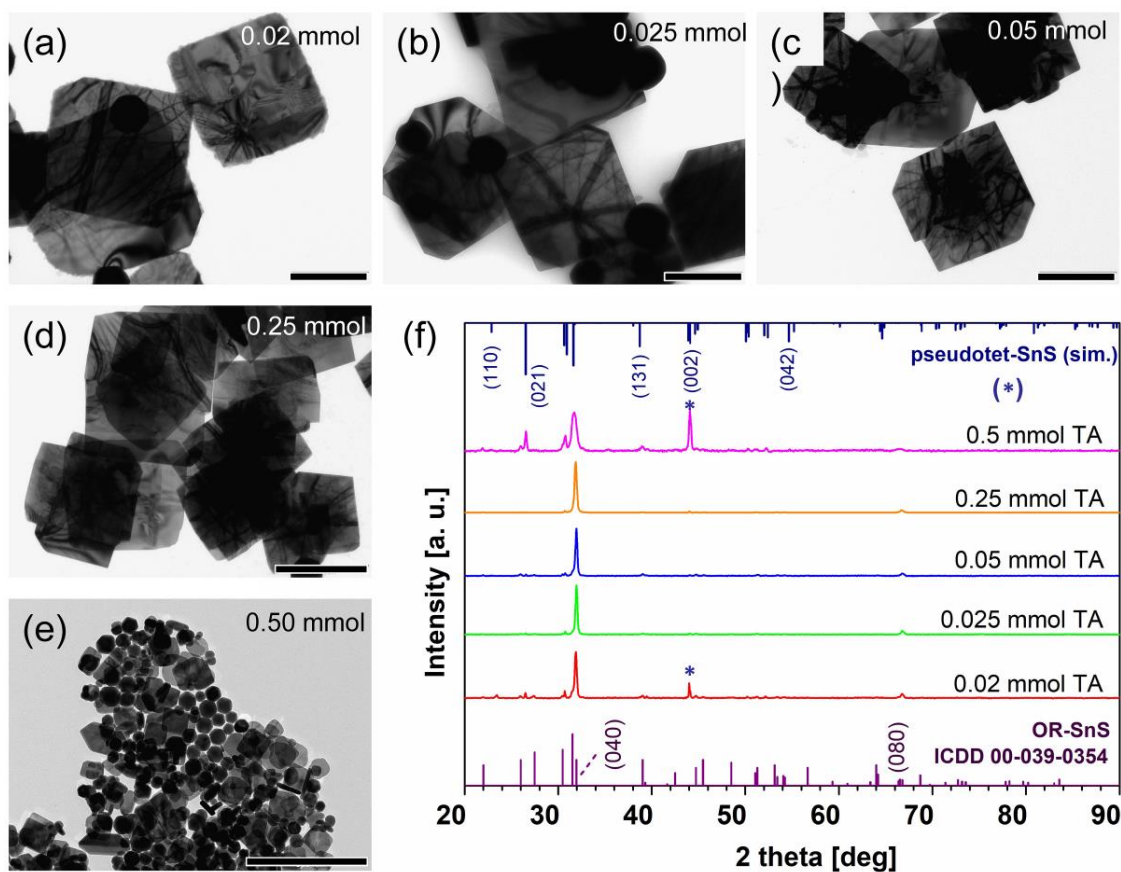


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406 **Figure 6.** Schematic illustration of the formation and shape evolution of SnS nanostructures.

407 LS=Lateral size, TN=Thickness.

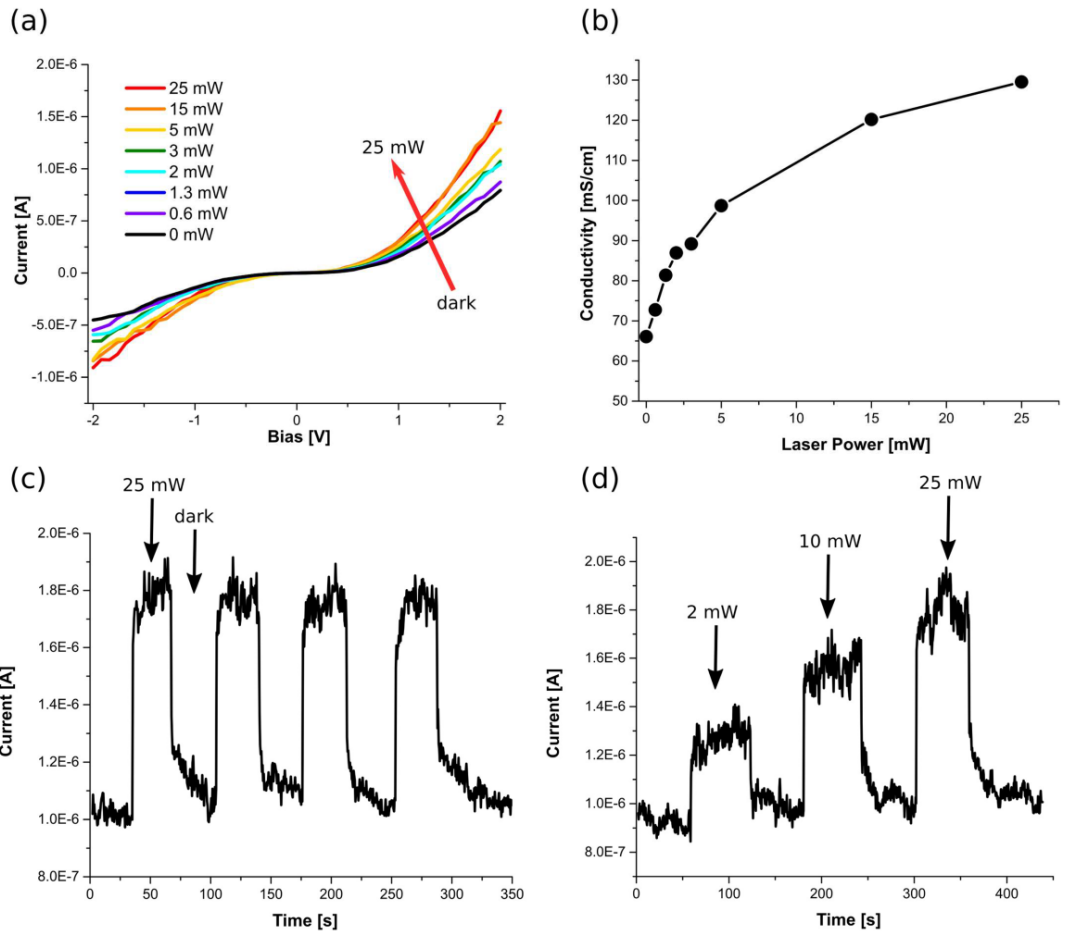
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410 **Figure 7.** (a-e) Shape and size change of 2D SnS nanoparticles to nanosheets synthesized
 411 using an amount of tin acetate from 0.02 mmol to 0.025, 0.05, 0.25, and 0.5 mmol. Scale bars
 412 correspond all to 500 nm. (f) Powder XRD patterns of SnS NSs from a-e.

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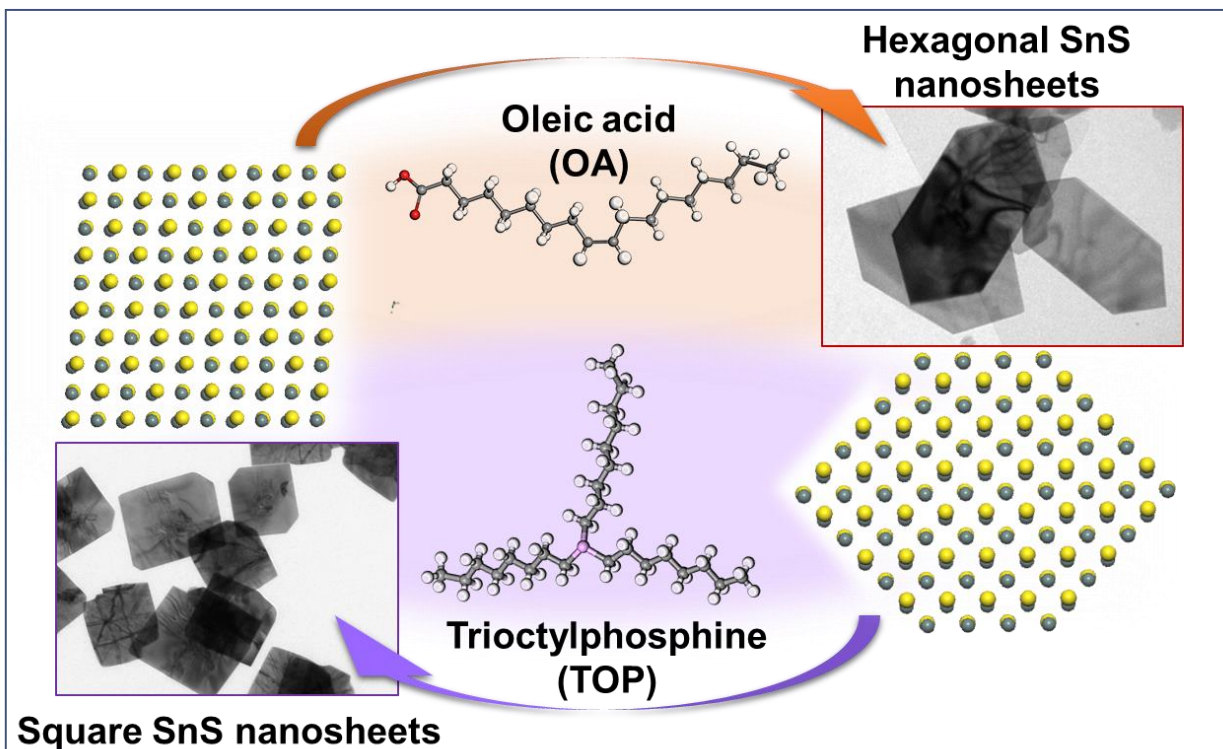
415 **Figure 8.** Photo-electrical properties of the nanosheets (a) I-V characteristics of the NSs in
 416 dark and under illumination with the red laser ($\lambda = 627$ nm) of various intensities. Higher
 417 currents are achieved under higher powers of illumination (b) Conductivity of the sheets in
 418 different laser powers. The photoconductivity increases by increasing the power and saturates
 419 in higher powers. (c) Stability of the photo-current under an intermittent illumination. By
 420 switching the 25 mW red laser on and off, stable photo-currents are achieved with fast
 421 transitions between the on state and the off state. (d) Intermittent illumination of the sheets
 422 with different powers. The photo-current can be tuned by the laser power, while the stability
 423 and the speed of the system are maintained.

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